

Substitute for form 1449A/PTO			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application / Conf. No.	Unknown /	
			Filing Date	October 24, 2003	
			First Named Inventor	Kevin T. Look	
			Art Unit	Unknown <i>2818</i>	
			Examiner Name	Unknown <i>V. Nguyen</i>	
Sheet	1	of	2	Attorney Docket Number	X-719-1D-3D US

U.S. PATENT DOCUMENTS					
Examiner Initials *	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code (if known)			
<i>UP</i>		US- 5,627,400	05-06-92	Koga	
<i>UP</i>		US- 5,656,528	08-12-97	Wahlstrom	
<i>UP</i>		US- 5,821,160	10-13-98	Rodriguez et al.	
<i>UP</i>		US- 5,972,756	10-26-99	Kono et al.	
<i>UP</i>		US- 6,235,574 B1	05-22-01	Tobben et al	
<i>UP</i>		US- 6,261,964 B1	07-17-01	Wu et al.	
<i>UP</i>		US- 6,495,424 B1	12-17-02	Kunikiyo	
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FOREIGN PATENT DOCUMENTS					
Examiner Initials *	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code ² - Number ³ - Kind Code ⁴ (if known)			
<i>UP</i>		JP 360009160 A	01-18-85	Matsushita Electric	
<i>UP</i>		JP 363079377 A	04-09-88	Oki Electric	
<i>UP</i>		JP 406163906 A	06-10-94	Sanyo Electric	
<i>UP</i>		JP 406232389 A	08-19-94	Kou	
<i>UP</i>		JP 408264660 A	10-11-96	NEC Corp.	
<i>UP</i>		JP 2000077356 A	03-14-00	Texas Instr.	

Examiner Signature	<i>V. Nguyen</i>	Date Considered	<i>8/18/04</i>
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¹ Applicant's unique citation designation number (optional). ² See Kinds of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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Sheet 2 of 2	Attorney Docket Number	X-719-1D-3D US	

OTHER -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No'	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T *
W		"Boron Diffusion And Penetration In Ultrathin Oxide With Poly-Si Gate"; Cao et al.; IEEE Electron Device Letters; Vol. 19; No. 8; August 1998; pp. 291-293.	
W		Aoyama et al.; "Flat-band Voltage Shifts In P-MOS Devices Caused By Carrier Activation In P+-Polycrystalline Silicon and Boron Penetration"; 1997 IEEE; pp. 26.1.1 - 26.1.4.	
W		Alavi et al.; "A PROM Element Based On Salicide Agglomeration Of Poly Fuses In A CMOS Logic Process"; 1997 IEEE; pp. 34.3.1 - 34.3.4	
W		Jang et al.; "Effects Of Thermal Processes After Silicidation On The Performance Of TiSi ₂ /Polysilicon Gate Device"; IEEE Transactions On Electron Devices; Vol. 46; No. 12; December 1999; pp. 2353 -2356.	
W		Lasky et al.; "Comparison Of Transformation To Low-Resistivity Phase And Agglomeration Of TiSi ₂ and CoSi ₂ "; IEEE Transaction On Electron Devices; Vol. 38; No. 2; February 1991; pp. 262-269.	
W		Kalnitsky et al.; "CoSi ₂ Integrated Fuses On Poly Silicon For Low Voltage 0.18 um CMOS Application"; 1999 IEEE; 4 pages.	
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Examiner Signature	V. Nguyen	Date Considered	8/18/09
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